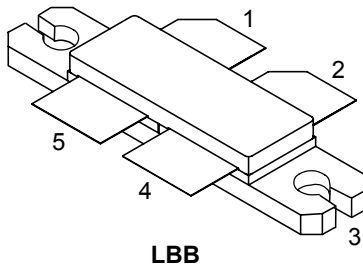


120 W 50 V RF power LDMOS transistor from HF to 1.5 GHz



Pin connection	
Pin	Connection
1	Drain A
2	Drain B
3	Source (bottom side)
4	Gate B
5	Gate A

Features

Order code	Frequency	V _{DD}	P _{OUT}	Gain	Efficiency
RF5L15120CB4	1000 MHz	50 V	120 W	20 dB	60%

- High efficiency and linear gain operations
- Integrated ESD protection
- Large positive and negative gate/source voltage range
- Excellent thermal stability, low HCI drift
- In compliance with the european directive 2002/95/EC

Applications

- Broadband commercial communications
- TV broadcast
- Avionics
- Industrial

Description

The RF5L15120CB4 is a 120 W LDMOS FET, designed for broadband commercial communications, TV Broadcast, Avionics and industrial applications with frequencies from HF to 1.5 GHz. It can be used in class AB/B and class C for all typical modulation formats.



Product status link
RF5L15120CB4

Product summary	
Order code	RF5L15120CB4
Marking	RF5L15120CB4
Package	LBB
Packing	Tape and reel 13"
Base/bulk quantity	100/100

1 Electrical data

1.1 Absolute ratings

Table 1. Absolute maximum ratings ($T_{CASE} = 25\text{ °C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-source voltage	95	V
V_{GS}	Gate-source voltage	-8/+10	V
V_{DD}	Maximum operating voltage	55	V
T_J	Maximum junction temperature	+200	°C
T_{STG}	Storage temperature range	-65 to +150	°C

1.2 Thermal data

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Junction-case thermal resistance	0.7	°C/W

Note: $T_{CASE} = +85\text{ °C}$, $T_J = +200\text{ °C}$, DC test.

1.3 ESD protection characteristics

Table 3. ESD protection

Symbol	Test methodology	Class
HBM	Human body model (per JESD22-A114)	2

2 Electrical characteristics

2.1 Static

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_{DS} = 0.5\text{ mA}$	95			V
I_{DSS}	Zero gate voltage drain leakage current	$V_{GS} = 0\text{ V}, V_{DS} = 90\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}$				
I_{GSS}	Gate-source leakage current	$V_{GS} = 10\text{ V}, V_{DS} = 0\text{ V}$			100	nA
		$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$				
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = 50\text{ V}, I_{DS} = 600\text{ }\mu\text{A}$	2		2.8	V
$V_{GS(Q)}$	Gate quiescent voltage	$V_{DS} = 50\text{ V}, I_{DS} = 400\text{ mA}$	2		6	V
$V_{DS(on)}$	Static drain-source on-voltage	$V_{GS} = 10\text{ V}, I_{DS} = 2\text{ A}$			1.2	V
$I_{DS(on)}$	Static drain-source on-current	$V_{GS} = 10\text{ V}, V_{DS} = 100\text{ mV}$			2.5	A
$R_{DS(on)}$	Drain-source on-state resistance	$V_{GS} = 10\text{ V}, V_{DS} = 100\text{ mV}$			1	Ω
C_{ISS}	Common source input capacitance	$V_{GS} = 0\text{ V}, V_{DD} = 50\text{ V},$ $f = 1\text{ MHz}$		56		pF
C_{RSS}	Common source feedback capacitance			0.6		pF
C_{OSS}	Common source output capacitance			23		pF

2.2 Dynamic

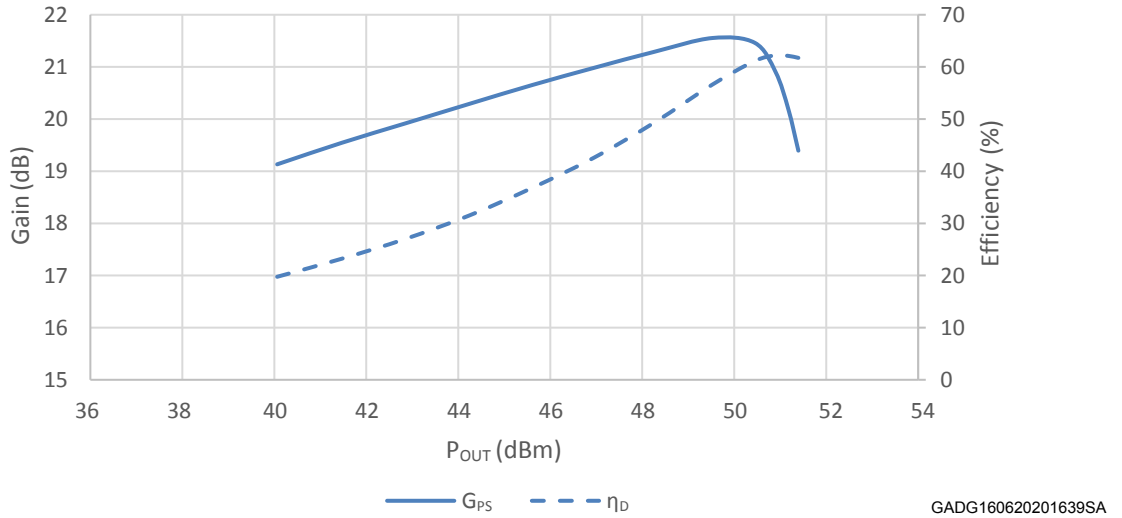
Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
f	Frequency				1500	MHz
P_{OUT}	Output power	f = 1000 MHz, at 1dB compression point, pulsed CW		120		W
G_{PS}	Power gain			20		dB
η_D	Drain efficiency			60		%
VSWR	Load mismatch	At 120 W pulsed CW output power, all phase angles			10:1	

Note: $V_{DD} = 50\text{ V}, I_{DQ} = 100\text{ mA},$ pulse width = 100 $\mu\text{s},$ duty cycle = 10%.

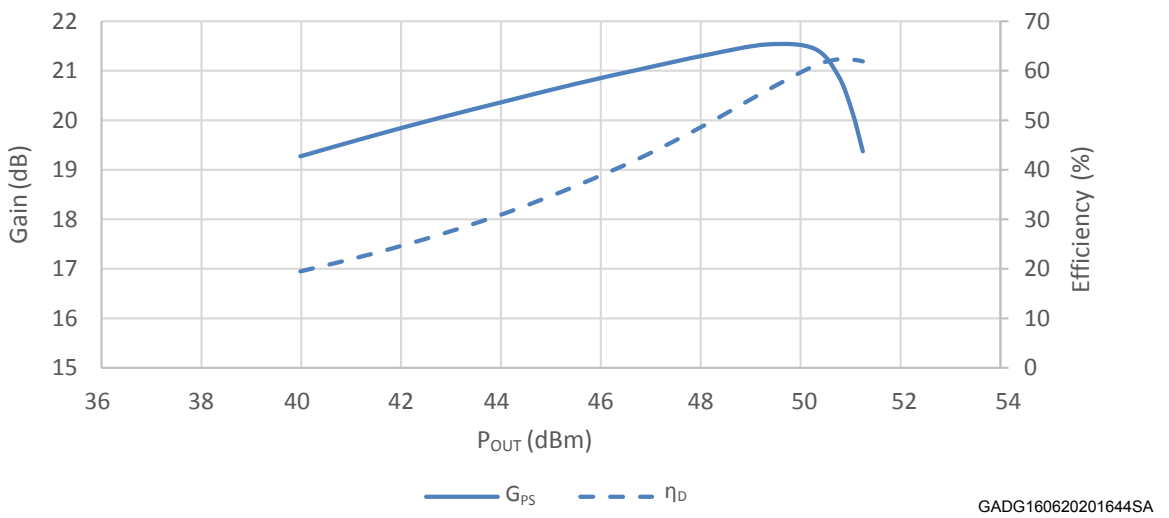
3 Typical performances

Figure 1. Power gain and drain efficiency versus output power (f = 1000 MHz, pulsed CW)



Note: $V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$, pulsed CW; pulse width = 100 μs , duty cycle = 10%.

Figure 2. Power gain and drain efficiency versus output power (f = 1000 MHz, CW)

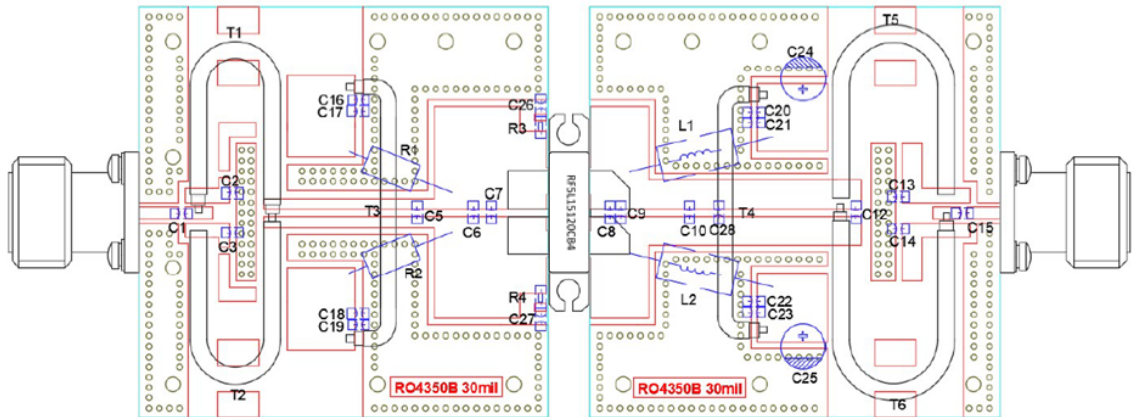


Note: $V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$.

4 Test circuit

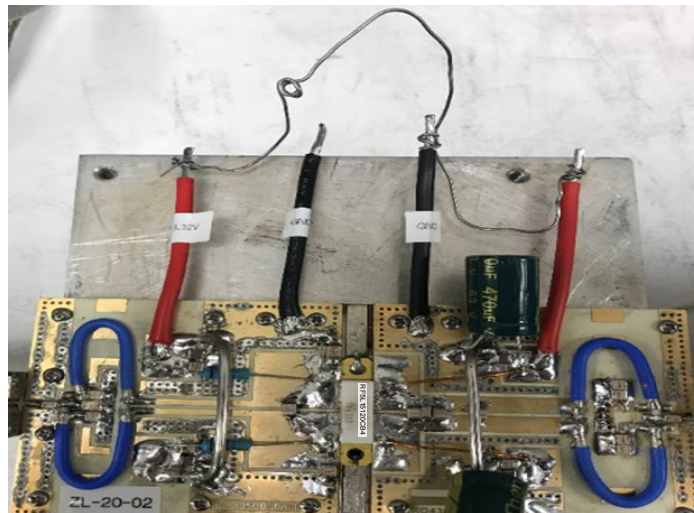
4.1 Test circuit layout

Figure 3. Test circuit layout (f = 1000 MHz)



GADG170620201720SA

Figure 4. Test circuit photo (f = 1000 MHz)



GADG160620201621SA

Table 6. Components list

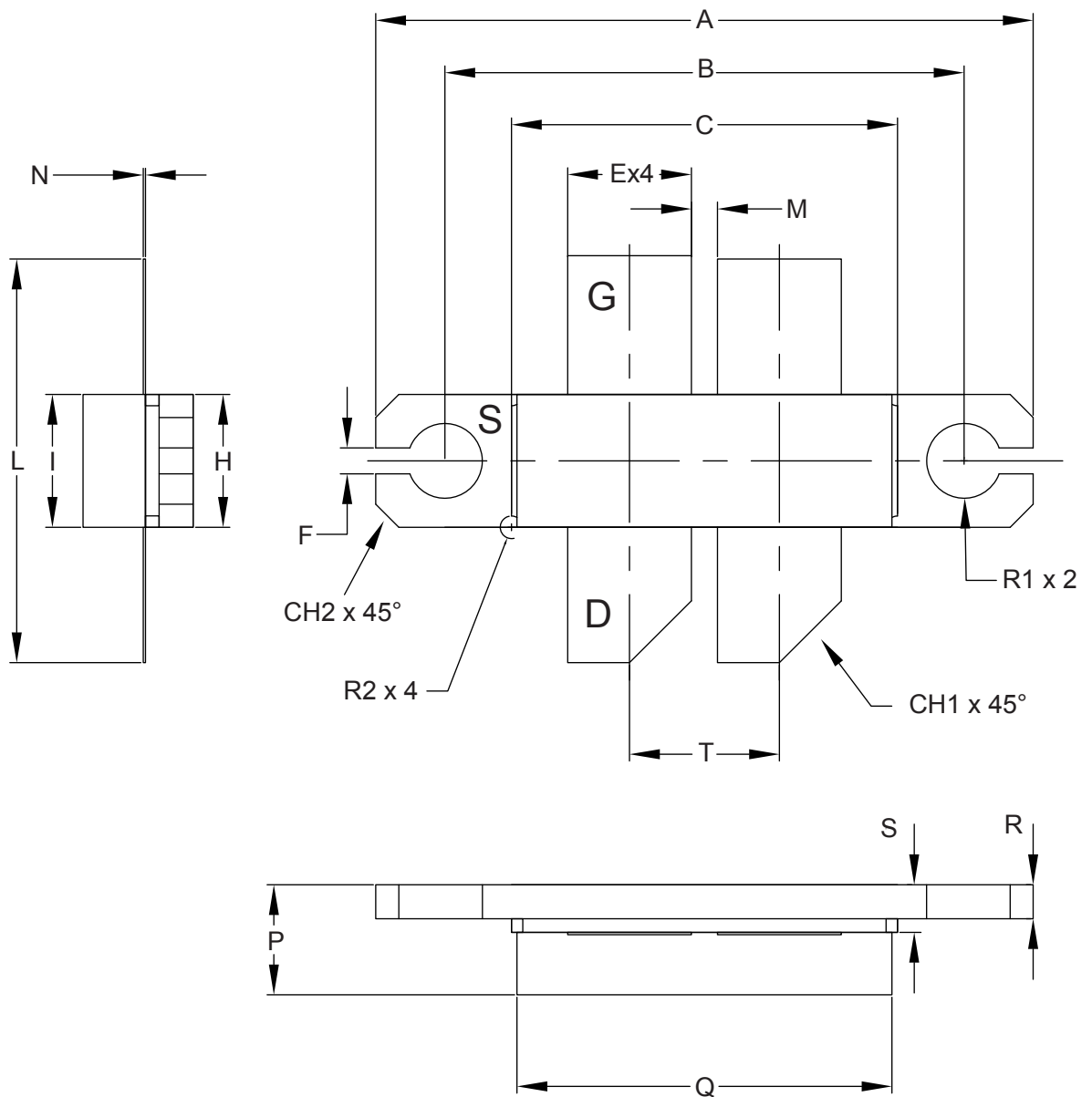
Component	Description	Suggested manufacturer
C1, C2, C3, C13, C14, C15, C17, C18, C21, C22, C26, C27	120 pF	ATC800B
C5	6.8 pF	ATC800B
C6	5.6 pF	ATC800B
C7	10 pF	ATC800B
C12	3.3 pF	ATC800B
C8, C9, C10, C28	8.2 pF	ATC800B
C16, C19, C20, C23	Ceramic multilayer capacitor, 10 μ F, 100 V	10 μ F/100 V
R1, R2	Metal film resistor, 200 Ω	
R4, R5	Chip resistor, 13 Ω , 1206	
L1, L2	Copper wire, cross section diameter 0.8 mm	
C24, C25	Electrolytic capacitor, 470 μ F, 63 V	
PCB	0.762 mm [0.030"] thick, $\epsilon_r= 3.48$, Rogers RO4350B, 1 oz. copper	

5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

5.1 LBB package information

Figure 5. LBB package outline



DM00666717_2

Table 7. LBB mechanical data

Symbol	Millimeters		
	Min.	Typ.	Max.
A	28.82	28.95	29.08
B	22.73	22.86	22.99
C	16.87	17.00	17.13
E	5.32	5.45	5.58
F	1.01	1.14	1.27
H	5.72	5.85	5.98
I	5.72	5.85	5.98
L	17.65	17.78	17.91
M	1.02	1.15	1.28
N		0.10	
P	4.72	4.85	4.98
Q	16.38	16.51	16.64
R	1.37	1.50	1.63
S	1.97	2.10	2.23
T		6.60	
CH1		2.72	
CH2		1.02	
R1		1.65	
R2		0.50	

Revision history

Table 8. Document revision history

Date	Version	Changes
16-Jun-2020	1	First release

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